

INTERFACE CIRCUITS

SERIES 55460/75460 DUAL PERIPHERAL DRIVERS

BULLETIN NO. DL-S 12425, DECEMBER 1976—REVISED AUGUST 1977

PERIPHERAL DRIVERS FOR HIGH-VOLTAGE, HIGH-CURRENT DRIVER APPLICATIONS

performance

- Characterized for Use to 300 mA
- High-Voltage Outputs
- No Output Latch-Up at 30 V (After Conducting 300 mA)
- Medium-Speed Switching

ease-of-design

- Circuit Flexibility for Varied Applications and Choice of Logic Function
- TTL- or DTL-Compatible Diode-Clamped Inputs
- Standard Supply Voltages
- Available in Plastic and Ceramic Packages

description

Series 55460/75460 dual peripheral drivers are functionally interchangeable with Series 55450B/75450B and Series 55460/75460 peripheral drivers, but are designed for use in systems that require higher breakdown voltages than either of those series can provide at the expense of slightly slower switching speeds. Typical applications include logic buffers, power drivers, relay drivers, lamp drivers, MOS drivers, line drivers, and memory drivers. Series 55460 drivers are characterized for operation over the full military temperature range of -55°C to 125°C ; Series 75460 drivers are characterized for operation from 0°C to 70°C .

The SN55460 and SN75460 are unique general-purpose devices each featuring two standard Series 54/74 TTL gates and two uncommitted, high-current, high-voltage, n-p-n transistors. These devices offer the system designer the flexibility of tailoring the circuit to the application.

The SN55461/SN75461, SN55462/SN75462, SN55463/SN75463, and SN55464/SN75464 are dual peripheral AND, NAND, OR, and NOR drivers, respectively, (assuming positive logic) with the output of the gates internally connected to the bases of the n-p-n output transistors.

SUMMARY OF SERIES 55460/75460

DEVICE	LOGIC OF COMPLETE CIRCUIT	PACKAGES
SN55460	AND [†]	J
SN55461	AND	JG
SN55462	NAND	JG
SN55463	OR	JG
SN55464	NOR	JG
SN75460	AND [†]	J, N
SN75461	AND	JG, P
SN75462	NAND	JG, P
SN75463	OR	JG, P
SN75464	NOR	JG, P

[†]With output transistor base connected externally to output of gate.

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SERIES 55460/75460 DUAL PERIPHERAL DRIVERS

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

	SN55460	SN55461 SN55462 SN55463 SN55464	SN75460	SN75461 SN75462 SN75463 SN75464	UNIT
Supply voltage, V_{CC} (see Note 1)	7	7	7	7	V
Input voltage	5.5	5.5	5.5	5.5	V
Interemitter voltage (see Note 2)	5.5	5.5	5.5	5.5	V
V_{CC} -to-substrate voltage	40		40		V
Collector-to-substrate voltage	40		40		V
Collector-base voltage	40		40		V
Collector-emitter voltage (see Note 3)	40		40		V
Collector-emitter voltage (see Note 4)	25		25		V
Emitter-base voltage	5		5		V
Off-state output voltage		35		35	V
Continuous collector or output current (see Note 5)	400	400	400	400	mA
Peak collector or output current ($t_W \leq 10$ ms, duty cycle $\leq 50\%$, see Note 5)	500	500	500	500	mA
Continuous total dissipation at (or below) 25°C free-air temperature (see Note 6)	J package JG package N package P package	1375 1050 1150 1000	1025 825 1150 1000		mW
Operating free-air temperature range		-55 to 125	-55 to 125	0 to 70	0 to 70
Storage temperature range		-65 to 150	-65 to 150	-65 to 150	-65 to 150
Lead temperature 1/16 inch from case for 60 seconds	J or JG package	300	300	300	300
Lead temperature 1/16 inch from case for 10 seconds	N or P package	260	260	260	260

- NOTES: 1. Voltage values are with respect to network ground terminal unless otherwise specified.
 2. This is the voltage between two emitters of a multiple-emitter transistor.
 3. This value applies when the base-emitter resistance (R_{BE}) is equal to or less than 500 Ω .
 4. This value applies between 0 and 10 mA collector current when the base-emitter diode is open-circuited.
 5. Both halves of these dual circuits may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation rating.
 6. For operation above 25°C free-air temperature, refer to Dissipation Derating Curves in the Thermal Information Section, which starts on page 11. In the J and JG packages, SN55460 through SN55464 chips are alloy-mounted; SN75460 through SN75464 chips are glass-mounted.

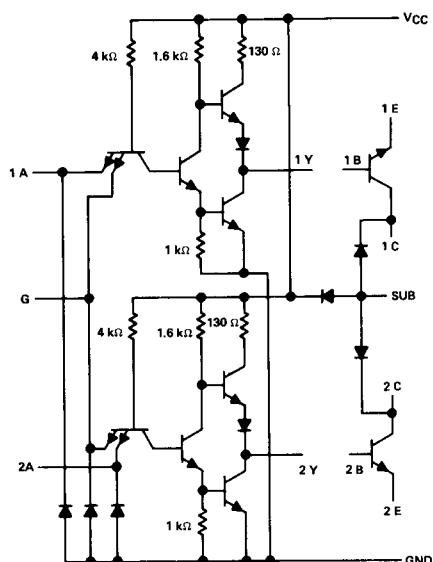
recommended operating conditions (see Note 7)

	SERIES 55460			SERIES 75460			UNIT
	MIN	NOM	MAX	MIN	NOM	MAX	
Supply voltage, V_{CC}	4.5	5	5.5	4.75	5	5.25	V
Operating free-air temperature, T_A	-55	125	0	70			C

NOTE 7: For SN55460 and SN75460 only, the substrate (pin 8) must always be at the most negative device voltage for proper operation.

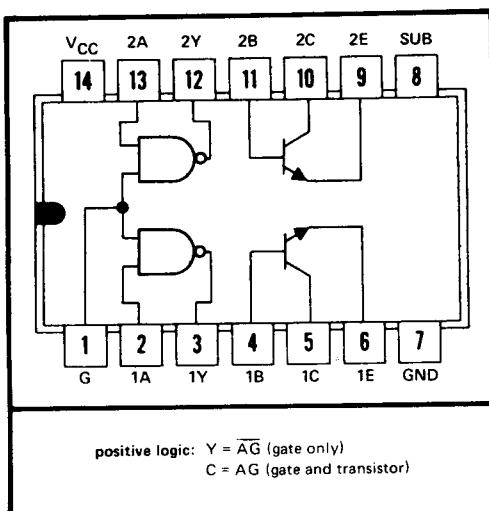
TYPES SN55460, SN75460 DUAL PERIPHERAL POSITIVE-AND DRIVERS

schematic



Resistor values shown are nominal.

SN55460 . . . J
SN75460 . . . J OR N
DUAL-IN-LINE PACKAGE (TOP VIEW)



positive logic: $Y = \overline{AG}$ (gate only)
 $C = AG$ (gate and transistor)

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

TTI gates

PARAMETER		TEST CONDITIONS [†]	SN55460			SN75460			UNIT
			MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
V _{IH}	High-level input voltage		2			2			V
V _{IL}	Low-level input voltage				0.8			0.8	V
V _{IK}	Input clamp voltage	V _{CC} = MIN, I _I = -12 mA		-1.2	-1.5		-1.2	-1.5	V
V _{OH}	High-level output voltage	V _{CC} = MIN, V _{IL} = 0.8 V, I _{OH} = -400 µA	2.4	3.3		2.4	3.3		V
V _{OL}	Low-level output voltage	V _{CC} = MIN, V _{IH} = 2 V, I _{OL} = 16 mA		0.25	0.5		0.25	0.4	V
I _I	Input current at maximum input voltage	input A	V _{CC} = MAX, V _I = 5.5 V			1			1
		input G				2			2 mA
I _{IH}	High-level input current	input A	V _{CC} = MAX, V _I = 2.4 V			40			40 µA
		input G				80			80 µA
I _{IL}	Low-level input current	input A	V _{CC} = MAX, V _I = 0.4 V			-1.6			-1.6 mA
		input G				-3.2			-3.2 mA
I _{OS}	Short-circuit output current [§]	V _{CC} = MAX	-18	-35	-55	-18	-35	-55	mA
I _{CCH}	Supply current, outputs high	V _{CC} = MAX, V _I = 0		2.8	4		2.8	4	mA
I _{CCL}	Supply current, outputs low	V _{CC} = MAX, V _I = 5 V		7	11		7	11	mA

[†] For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

[‡]All typical values at $V_{CC} = 5$ V, $T_A = 25^\circ\text{C}$.

§ Not more than one output should be shorted at a time.

TYPES SN55460, SN75460 DUAL PERIPHERAL POSITIVE-AND DRIVERS

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)
output transistors

PARAMETER	TEST CONDITIONS [†]	SN55460			UNIT
		MIN	TYP [‡]	MAX	
V(BR)CBO	Collector-Base Breakdown Voltage $I_C = 100 \mu A, I_E = 0$	40	40	40	V
V(BR)CEO	Collector-Emitter Breakdown Voltage $I_C = 10 mA, I_B = 0$, See Note 8	25	25	25	V
V(BR)CER	Collector-Emitter Breakdown Voltage $I_C = 100 \mu A, R_{BE} = 500 \Omega$	40	40	40	V
V(BR)EBO	Emitter-Base Breakdown Voltage $I_E = 100 \mu A, I_C = 0$	5	5	5	V
h_{FE}	Static Forward Current Transfer Ratio $V_{CE} = 3 V, I_C = 100 mA, T_A = 25^\circ C$	See Note 8	25	25	
			30	30	
			10	20	
			15	25	
V_{BE}	$I_B = 10 mA, I_C = 100 mA$	See Note 8	0.85	1.2	V
	$I_B = 30 mA, I_C = 300 mA$		1	1.4	
$V_{CE(sat)}$	$I_B = 10 mA, I_C = 100 mA$	See Note 8	0.25	0.5	V
	$I_B = 30 mA, I_C = 300 mA$		0.45	0.8	

[†]For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

[‡]All typical values are at $V_{CC} = 5 V, T_A = 25^\circ C$.

NOTE 8: These parameters must be measured using pulse techniques. $t_w = 300 \mu s$, duty cycle $\leq 2\%$.

switching characteristics, $V_{CC} = 5 V, T_A = 25^\circ C$

TTL gates

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output $C_L = 15 pF, R_L = 400 \Omega$, See Figure 1	22			ns
t_{PHL}	Propagation delay time, high-to-low-level output $C_L = 15 pF, R_L = 50 \Omega$, See Figure 1	8			ns

output transistors

PARAMETER	TEST CONDITIONS [‡]	MIN	TYP	MAX	UNIT
t_d	Delay time $I_C = 200 mA, I_B(1) = 20 mA, I_B(2) = -40 mA$	10			ns
t_r	Rise time $V_{BE(off)} = -1 V, C_L = 15 pF, R_L = 50 \Omega$	16			ns
t_s	Storage time See Figure 2	23			ns
t_f	Fall time	14			ns

*Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

gates and transistors combined

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t_{PLH}	Propagation delay time, low-to-high-level output $I_C \approx 200 mA, C_L = 15 pF, R_L = 50 \Omega$, See Figure 3	45	65	ns	
t_{PHL}	Propagation delay time, high-to-low-level output $I_C \approx 200 mA, C_L = 15 pF, R_L = 50 \Omega$, See Figure 3	35	50	ns	
t_{TLH}	Transition time, low-to-high-level output See Figure 3	10	20	ns	
t_{THL}	Transition time, high-to-low-level output See Figure 3	10	20	ns	
V_{OH}	High-level output voltage after switching $V_S = 30 V, I_C \approx 300 mA, R_{BE} = 500 \Omega$, See Figure 4	$V_S - 10$		mV	

TYPES SN55461, SN75461 DUAL PERIPHERAL POSITIVE-AND DRIVERS

logic

FUNCTION TABLE
(EACH DRIVER)

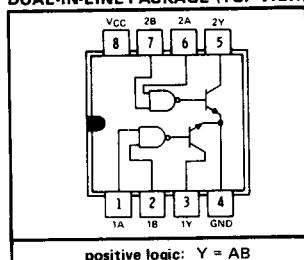
A	B	Y
L	L	L (on state)
L	H	L (on state)
H	L	L (on state)
H	H	H (off state)

H = high level, L = low level

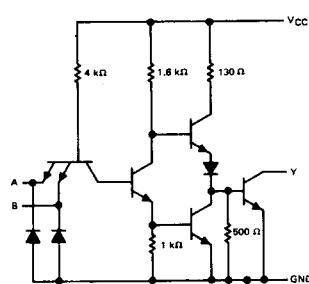
SN55461 . . . JG

SN75461 . . . JG OR P

DUAL-IN-LINE PACKAGE (TOP VIEW)



schematic (each driver)



Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	SN55461			SN75461			UNIT
		MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
V _{IH} High-level input voltage		2		2				V
V _{IL} Low-level input voltage			0.8			0.8		V
V _{IK} Input clamp voltage	V _{CC} = MIN, I _I = -12 mA	-1.2	-1.5		-1.2	-1.5		V
I _{OH} High-level output current	V _{CC} = MIN, V _{IH} = 2 V, V _{OH} = 35 V	300			100			μA
V _{OL} Low-level output voltage	V _{CC} = MIN, V _{IL} = 0.8 V, I _{OL} = 100 mA	0.25	0.5		0.25	0.4		V
	V _{CC} = MIN, V _{IL} = 0.8 V, I _{OL} = 300 mA	0.5	0.8		0.5	0.7		
I _I Input current at maximum input voltage	V _{CC} = MAX, V _I = 5.5 V	1		1				mA
I _{IH} High-level input current	V _{CC} = MAX, V _I = 2.4 V	40		40				μA
I _{IL} Low-level input current	V _{CC} = MAX, V _I = 0.4 V	-1	-1.6		-1	-1.6		mA
I _{CCH} Supply current, outputs high	V _{CC} = MAX, V _I = 5 V	8	11		8	11		mA
I _{CCL} Supply current, outputs low	V _{CC} = MAX, V _I = 0	56	76		56	76		mA

[†]For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

[‡]All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} Propagation delay time, low-to-high-level output	I _O ≈ 200 mA, C _L = 15 pF, R _L = 50 Ω, See Figure 3	30	55	ns	
t _{PHL} Propagation delay time, high-to-low-level output		25	40	ns	
t _{T LH} Transition time, low-to-high-level output		8	20	ns	
t _{THL} Transition time, high-to-low-level output		10	20	ns	
V _{OH} High-level output voltage after switching	V _S = 30 V, I _O ≈ 300 mA, See Figure 4	V _S -10			mV

TYPES SN55462, SN75462 DUAL PERIPHERAL POSITIVE-NAND DRIVERS

logic

FUNCTION TABLE
(EACH DRIVER)

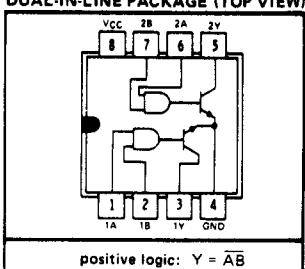
A	B	Y
L	L	H (off state)
L	H	H (off state)
H	L	H (off state)
H	H	L (on state)

H = high level, L = low level

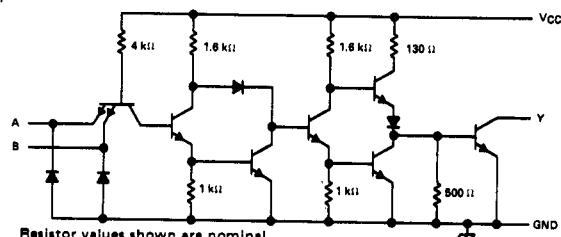
SN55462 . . . JG

SN75462 . . . JG OR P

DUAL-IN-LINE PACKAGE (TOP VIEW)



schematic (each driver)



Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	SN55462			SN75462			UNIT
		MIN	TYP†	MAX	MIN	TYP‡	MAX	
V _{IH}	High-level input voltage				2		2	V
V _{IL}	Low-level input voltage					0.8	0.8	V
V _{IK}	Input clamp voltage	V _{CC} = MIN, I _I = -12 mA			-1.2	-1.5	-1.2	V
I _{OH}	High-level output current	V _{CC} = MIN, V _{IL} = 0.8 V, V _{OH} = 35 V			300		100	μA
V _{OL}	Low-level output voltage	V _{CC} = MIN, V _{IH} = 2 V, I _{OL} = 100 mA	0.25	0.5	0.25	0.4		V
		V _{CC} = MIN, V _{IH} = 2 V, I _{OL} = 300 mA	0.5	0.8	0.5	0.7		
I _I	Input current at maximum input voltage	V _{CC} = MAX, V _I = 5.5 V		1		1	mA	
I _{IH}	High-level input current	V _{CC} = MAX, V _I = 2.4 V		40		40	μA	
I _{IL}	Low-level input current	V _{CC} = MAX, V _I = 0.4 V	-1.1	-1.6	-1.1	-1.6	mA	
I _{CCH}	Supply current, outputs high	V _{CC} = MAX, V _I = 0 V	13	17	13	17	mA	
I _{CCL}	Supply current, outputs low	V _{CC} = MAX, V _I = 5 V	61	76	61	76	mA	

†For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

‡All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

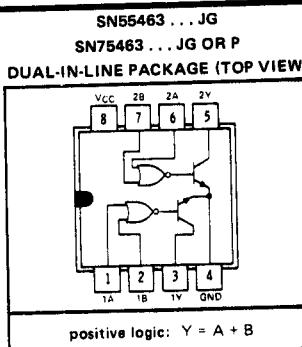
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output	I _O ≈ 200 mA, C _L = 15 pF, R _L = 50 Ω, See Figure 3	45	65	ns
t _{PHL}	Propagation delay time, high-to-low-level output		30	50	ns
t _{T LH}	Transition time, low-to-high-level output		13	25	ns
t _{THL}	Transition time, high-to-low-level output		10	20	ns
V _{OH}	High-level output voltage after switching	V _S = 30 V, I _O ≈ 300 mA, See Figure 4	V _S -10		mV

TYPES SN55463, SN75463 DUAL PERIPHERAL POSITIVE-OR DRIVERS

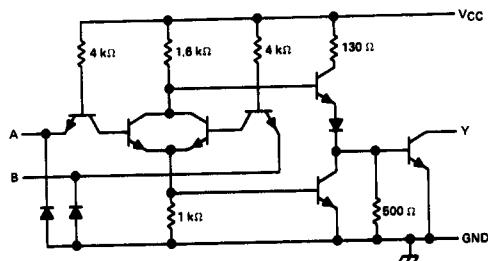
logic

FUNCTION TABLE (EACH DRIVER)		
A	B	Y
L	L	L (on state)
L	H	H (off state)
H	L	H (off state)
H	H	H (off state)

H = high level, L = low level



schematic (each driver)



Resistor values shown are nominal.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	SN55463			SN75463			UNIT
		MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
V _{IH}	High-level input voltage		2		2		2	V
V _{IL}	Low-level input voltage			0.8			0.8	V
V _{IK}	Input clamp voltage	V _{CC} = MIN, I _I = -12 mA	-1.2	-1.5	-1.2	-1.5	-1.2	V
I _{OH}	High-level output current	V _{CC} = MIN, V _{IH} = 2 V, V _{OH} = 35 V		300			100	μA
V _{OL}	Low-level output voltage	V _{CC} = MIN, V _{IL} = 0.8 V, I _{OL} = 100 mA	0.25	0.5	0.25	0.4		V
		V _{CC} = MIN, V _{IL} = 0.8 V, I _{OL} = 300 mA	0.5	0.8	0.5	0.7		
I _I	Input current at maximum input voltage	V _{CC} = MAX, V _I = 5.5 V		1			1	mA
I _{IH}	High-level input current	V _{CC} = MAX, V _I = 2.4 V		40			40	μA
I _{IL}	Low-level input current	V _{CC} = MAX, V _I = 0.4 V	-1	-1.6	-1	-1.6	-1	mA
I _{CCH}	Supply current, outputs high	V _{CC} = MAX, V _I = 5 V	8	11	8	11	8	mA
I _{CCL}	Supply current, outputs low	V _{CC} = MAX, V _I = 0	58	76	58	76	58	mA

[†]For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

[‡]All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH}	Propagation delay time, low-to-high-level output t _{PHL} Propagation delay time, high-to-low-level output t _{TLH} Transition time, low-to-high-level output t _{THL} Transition time, high-to-low-level output	I _O ≈ 200 mA, C _L = 15 pF, R _L = 50 Ω, See Figure 3	30	55	ns
t _{PLH}			25	40	ns
t _{TLH}			8	25	ns
t _{THL}			10	25	ns
V _{OH}	High-level output voltage after switching	V _S = 30 V, I _O ≈ 300 mA, See Figure 4	V _S -10		mV

TYPES SN55464, SN75464 DUAL PERIPHERAL POSITIVE-NOR DRIVERS

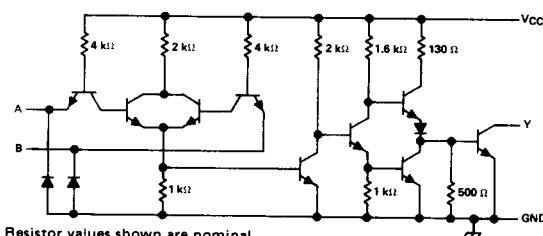
logic

FUNCTION TABLE
(EACH DRIVER)

A	B	Y
L	L	H (off state)
L	H	L (on state)
H	L	L (on state)
H	H	L (on state)

H = high level, L = low level

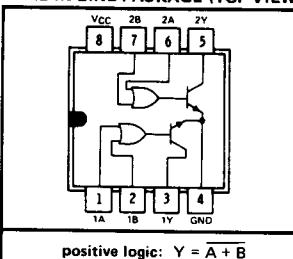
schematic (each driver)



SN55464 . . . JG

SN75464 . . . JG OR P

DUAL-IN-LINE PACKAGE (TOP VIEW)



positive logic: $Y = A + B$

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS [†]	SN55464			SN75464			UNIT
		MIN	TYP [‡]	MAX	MIN	TYP [‡]	MAX	
V _{IH} High-level input voltage		2		2				V
V _{IL} Low-level input voltage				0.8			0.8	V
V _{IK} Input clamp voltage	V _{CC} = MIN, I _I = -12 mA	-1.2	-1.5		-1.2	-1.5		V
I _{OH} High-level output current	V _{CC} = MIN, V _{IL} = 0.8 V, V _{OH} = 25 V		300			100		μA
V _{OL} Low-level output voltage	V _{CC} = MIN, V _{IH} = 2 V, I _{OL} = 100 mA	0.25	0.5	0.25	0.4			V
	V _{CC} = MIN, V _{IH} = 2 V, I _{OL} = 300 mA	0.5	0.8	0.5	0.7			
I _I Input current at maximum input voltage	V _{CC} = MAX, V _I = 5.5 V	1		1				mA
I _{IH} High-level input current	V _{CC} = MAX, V _I = 2.4 V		40			40		μA
I _{IL} Low-level input current	V _{CC} = MAX, V _I = 0.4 V	-1	-1.6		-1	-1.6		mA
I _{CCH} Supply current, outputs high	V _{CC} = MAX, V _I = 0 V	14	19		14	19		mA
I _{CCL} Supply current, outputs low	V _{CC} = MAX, V _I = 5 V	67	85		67	85		mA

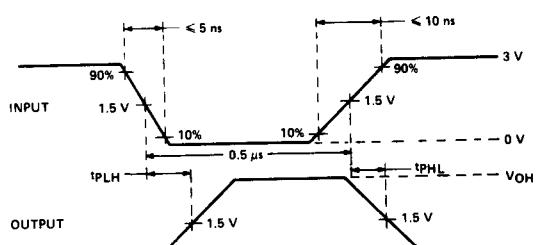
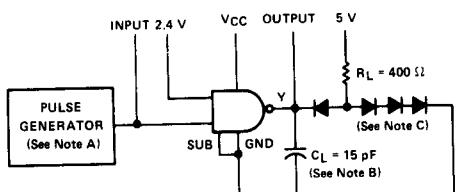
[†]For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.
[‡]All typical values are at V_{CC} = 5 V, T_A = 25°C.

switching characteristics, V_{CC} = 5 V, T_A = 25°C

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} Propagation delay time, low-to-high-level output		40	65	ns	
t _{PHL} Propagation delay time, high-to-low-level output	I _O ≈ 200 mA, C _L = 15 pF, R _L = 50 Ω, See Figure 3	30	50	ns	
t _{T LH} Transition time, low-to-high-level output		8	20	ns	
t _{THL} Transition time, high-to-low-level output		10	20	ns	
V _{OH} High-level output voltage after switching	V _S = 30 V, I _O ≈ 300 mA, See Figure 4	V _S -10			mV

**SERIES 55460/75460
DUAL PERIPHERAL DRIVERS**

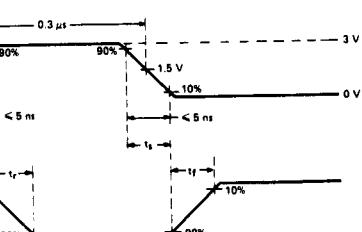
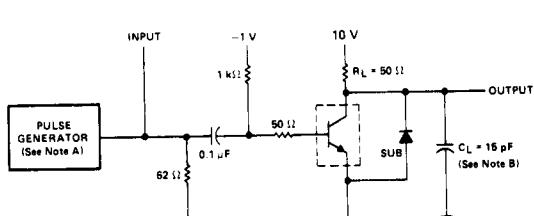
PARAMETER MEASUREMENT INFORMATION



TEST CIRCUIT

NOTES: A. The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{out} \approx 50 \Omega$.
B. C_L include probe and jig capacitance.
C. All diodes are 1N3064.

FIGURE 1—PROPAGATION DELAY TIMES, EACH GATE (SN55460 AND SN75460 ONLY)



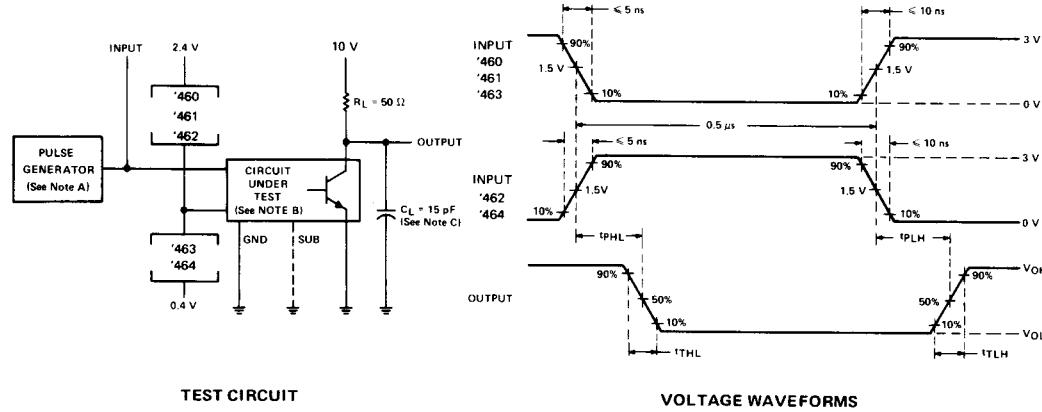
TEST CIRCUIT

NOTES: A. The pulse generator has the following characteristics: duty cycle $\leq 1\%$, $Z_{out} \approx 50 \Omega$.
B. C_1 includes probe and jig capacitance.

FIGURE 2—SWITCHING TIMES, EACH TRANSISTOR (SN55460 AND SN75460 ONLY)

SERIES 55460/75460 DUAL PERIPHERAL DRIVERS

PARAMETER MEASUREMENT INFORMATION

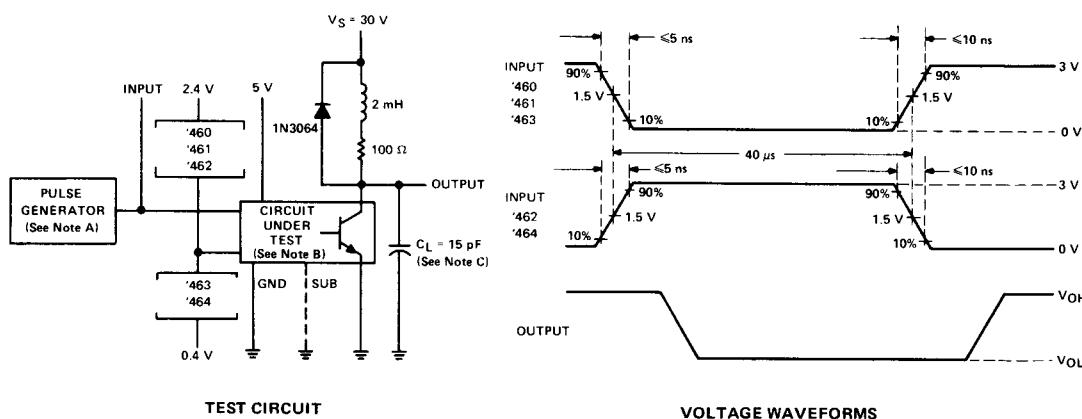


TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{out} \approx 50 \Omega$.
B. When testing SN55460 or SN75460, connect output Y to transistor base and ground the substrate terminal.
C. C_L includes probe and jig capacitance.

FIGURE 3—SWITCHING TIMES OF COMPLETE DRIVERS



TEST CIRCUIT

VOLTAGE WAVEFORMS

NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_{out} = 50 \Omega$.
B. When testing SN55460 or SN75460, connect output Y to transistor base with a 500- Ω resistor from there to ground, and ground the substrate terminal.
C. C_L includes probe and jig capacitance.

FIGURE 4—LATCH-UP TEST OF COMPLETE DRIVERS